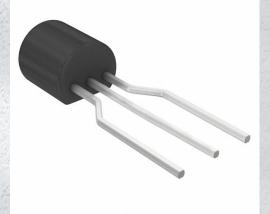


# **BF421ZL1 Datasheet**

www.digi-electronics.com



DiGi Electronics Part Number	BF421ZL1-DG
Manufacturer	onsemi
Manufacturer Product Number	BF421ZL1
Description	TRANS PNP 300V 0.05A TO92
Detailed Description	Bipolar (BJT) Transistor PNP 300 V 50 mA 60MHz 83 0 mW Through Hole TO-92 (TO-226)

https://www.DiGi-Electronics.com



Tel: +00 852-30501935

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# Purchase and inquiry

BF421ZL1     onsemi       BF42     onsemi		
Series:Product Status:ObsoleteTransistor Type:Current - Collector (IC) (Max):PNP50 mAVoltage - Collector Emitter Breakdown (Max):Vce Saturation (Max) @ lb, Ic:800 V500mV @ 2mA, 20mACurrent - Collector Cutoff (Max):S00mV @ 2mA, 20mACurrent - Collector Cutoff (Max):S0 @ 25mA, 20VPower - Max:Frequency - Transition:830 mW60MHzOperating Temperature:Mounting Type:55°C ~ 150°C (TJ)Through HolePackage / Case:Supplier Device Package:Power - Supplier Device Package:To-92 (To-226)	Manufacturer Product Number:	Manufacturer:
Construction     Obsolete       Transistor Type:     Current - Collector (Ic) (Max):       PNP     S0 mA       Voltage - Collector Emitter Breakdown (Max):     Vce Saturation (Max)@ Ib, Ic:       S00 V     S00mV@ 2mA, 20mA       Current - Collector Cutoff (Max):     DC Current Gain (hFE) (Min)@ Ic, Vce:       Current - Collector Cutoff (Max):     S0 @ 25mA, 20V       Power - Max:     Frequency - Transition:       S00 MW     GMHz       S00 mW     Mounting Type:       S00 mW     Transition:       S00 mW     S00Hz       S00 mW     S00 mW       S00 mW     S00 mW  <	BF421ZL1	onsemi
Transistor Type:Current - Collector (Ic) (Max):PNP50 mA/oltage - Collector Emitter Breakdown (Max):Vce Saturation (Max) @ Ib, Ic:200 V500mV @ 2mA, 20mACurrent - Collector Cutoff (Max):DC Current Gain (hFE) (Min) @ Ic, Vce:Current - Collector Cutoff (Max):50 @ 25mA, 20VPower - Max:60MHz200 Preating Temperature:Munting Type:25°C ~ 15°C (TJ)Through HolePackage / Case:Supplier Device Package:200 Provee - Max:Supplier Device Package:200 Prove	Series:	Product Status:
PNP50 mAvoltage - Collector Emitter Breakdown (Max):Vce Saturation (Max)@lb, Ic:200 V500mV@2mA, 20mACurrent - Collector Cutoff (Max):Dc Current Gain (hFE) (Min)@lc, Vce:Current - Collector Cutoff (Max):50@ 25mA, 20VPower - Max:Frequency - Transition:200 W60MHzDerating Temperature:Mounting Type:55% ~ 150% (Tj)Through HolePackage / Case:Supplier Device Package:To-226-3, TO-92-3 Long Body (Formed Leads)To-92 (TO-226)		Obsolete
Avitage - Collector Emitter Breakdown (Max):Vce Saturation (Max) @ lb, Ic:300 V500mV @ 2mA, 20mACurrent - Collector Cutoff (Max):DC Current Gain (hFE) (Min) @ lc, Vce:10nA (ICBO)50 @ 25mA, 20VPower - Max:Frequency - Transition:300 W60MHzOperating Temperature:Mounting Type:55°C ~ 150°C (TJ)Through HolePackage / Case:Supplier Device Package:10-226-3, T0-92-3 Long Body (Formed Leads)To-92 (T0-226)	Transistor Type:	Current - Collector (Ic) (Max):
BOD V500mV @ 2mA, 20mACurrent - Collector Cutoff (Max):DC Current Gain (hFE) (Min) @ Ic, Vce:IOnA (ICBO)50 @ 25mA, 20VPower - Max:Frequency - Transition:B30 mW60MHzOperating Temperature:Mounting Type:55°C ~ 150°C (TJ)Through HolePackage / Case:Supplier Device Package:TO-226-3, TO-92-3 Long Body (Formed Leads)TO-92 (TO-226)	PNP	50 mA
Current - Collector Cutoff (Max):   DC Current Gain (hFE) (Min)@lc, Vce:     IOnA (ICBO)   50 @ 25mA, 20V     Power - Max:   Frequency - Transition:     330 mW   60MHz     Operating Temperature:   Mounting Type:     55°C ~ 150°C (TJ)   Through Hole     Package / Case:   Supplier Device Package:     TO-226-3, TO-92-3 Long Body (Formed Leads)   TO-92 (TO-226)	Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
In On A (ICBO)50 @ 25mA, 20VPower - Max:Frequency - Transition:330 mW60MHzOperating Temperature:Mounting Type:55°C ~ 150°C (TJ)Through HolePackage / Case:Supplier Device Package:TO-226-3, TO-92-3 Long Body (Formed Leads)TO-92 (TO-226)	300 V	500mV @ 2mA, 20mA
Power - Max:Frequency - Transition:830 mW60MHzOperating Temperature:Mounting Type:55°C ~ 150°C (TJ)Through HolePackage / Case:Supplier Device Package:TO-226-3, TO-92-3 Long Body (Formed Leads)TO-92 (TO-226)	Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ lc, Vce:
B30 mW 60MHz   Operating Temperature: Mounting Type:   55°C ~ 150°C (TJ) Through Hole   Package / Case: Supplier Device Package:   TO-226-3, TO-92-3 Long Body (Formed Leads) TO-92 (TO-226)	10nA (ICBO)	50 @ 25mA, 20V
Operating Temperature: Mounting Type:   55°C ~ 150°C (TJ) Through Hole   Package / Case: Supplier Device Package:   TO-226-3, TO-92-3 Long Body (Formed Leads) TO-92 (TO-226)	Power - Max:	Frequency - Transition:
255°C ~ 150°C (TJ) Through Hole   Package / Case: Supplier Device Package:   TO-226-3, TO-92-3 Long Body (Formed Leads) TO-92 (TO-226)	830 mW	60MHz
Package / Case:Supplier Device Package:TO-226-3, TO-92-3 Long Body (Formed Leads)TO-92 (TO-226)	Operating Temperature:	Mounting Type:
TO-226-3, TO-92-3 Long Body (Formed Leads) TO-92 (TO-226)	-55°C ~ 150°C (TJ)	Through Hole
	Package / Case:	Supplier Device Package:
Base Product Number:	TO-226-3, TO-92-3 Long Body (Formed Leads)	ТО-92 (ТО-226)
	Base Product Number:	
3F421	BF421	

# **Environmental & Export classification**

RoHS Status:	Moisture Sensitivity Level (MSL):
RoHS non-compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.21.0095	

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# **High Voltage Transistors**

## **PNP Silicon**

#### Features

• These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS

Rating	Symbol	BF421	BF423	Unit
Collector – Emitter Voltage	V <sub>CEO</sub>	-300	-250	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	-300	-250	Vdc
Emitter – Base Voltage	V <sub>EBO</sub>	-5	5.0	Vdc
Collector Current – Continuous	Ι <sub>C</sub>	-5	00	mAdc
Collector Current – Peak	I <sub>CM</sub>	10	00	mA
Total Device Dissipation (Note 1) @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	83 6.		mW mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	– 55 to	9 +150	°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Мах	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\thetaJA}$	150	°C/W
Thermal Resistance, Junction-to-Lead	$R_{\theta JL}$	68	°C/W

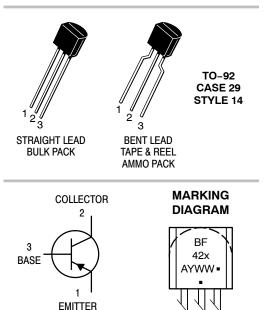
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

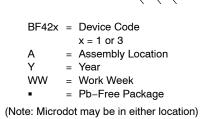
1. Mounted on a FR4 board with 200 mm<sup>2</sup> of 1 oz copper and lead length of 5 mm.



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#### ORDERING INFORMATION

Device	Package	Shipping
BF421ZL1G	TO–92 (Pb–Free)	2000/Ammo Pack
BF423G	TO-92 (Pb-Free)	5000 Units/Box
BF423ZL1G	TO-92 (Pb-Free)	2000/Ammo Pack

\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (Note 1) $(I_C = -1.0 \text{ mAdc}, I_B = 0)$	BF421 BF423	V <sub>(BR)CEO</sub>	-300 -250		Vdc
Collector – Base Breakdown Voltage ( $I_C = -100 \ \mu Adc$ , $I_E = 0$ )	BF421 BF423	V <sub>(BR)CBO</sub>	-300 -250		Vdc
Emitter – Base Breakdown Voltage ( $I_E = -100 \ \mu Adc, I_C = 0$ )	BF421 BF423	V <sub>(BR)EBO</sub>	-5.0 -5.0		Vdc
Collector Cutoff Current (V <sub>CB</sub> = -200 Vdc, I <sub>E</sub> = 0)	BF421 BF423	I <sub>CBO</sub>		-0.01 -	μAdc
Emitter Cutoff Current (V <sub>EB</sub> = -5.0 Vdc, I <sub>C</sub> = 0)	BF421 BF423	I <sub>EBO</sub>		-100 -	nAdc
ON CHARACTERISTICS					
DC Current Gain (I <sub>C</sub> = -25 mA, V <sub>CE</sub> = -20 Vdc)	BF421 BF423	h <sub>FE</sub>	50 50		-
Collector – Emitter Saturation Voltage $(I_C = -20 \text{ mAdc}, I_B = -2.0 \text{ mAdc})$		V <sub>CE(sat)</sub>	_	-0.5	Vdc
Base – Emitter Saturation Voltage $(I_C = -20 \text{ mA}, I_B = -2.0 \text{ mA})$		V <sub>BE(sat)</sub>	_	-2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				•	
Current – Gain – Bandwidth Product (I <sub>C</sub> = –10 mAdc, V <sub>CE</sub> = –10 Vdc, f = 20 MHz)		f <sub>T</sub>	60	-	MHz
Common Emitter Feedback Capacitance $(V_{CB} = -30 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$		C <sub>re</sub>	-	2.8	pF

1. Pulse Test: Pulse Width  $\leq$  300 µs; Duty Cycle  $\leq$  2.0%.

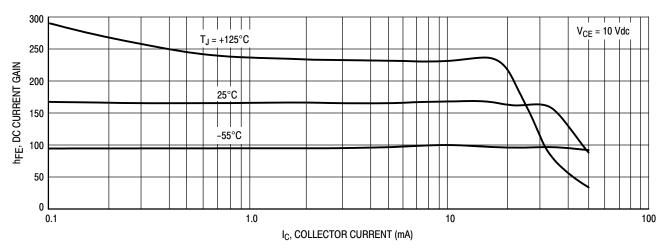


Figure 1. DC Current Gain

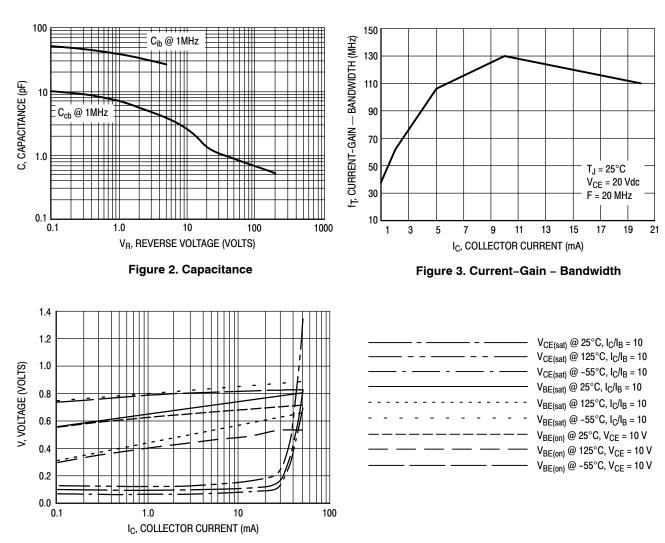
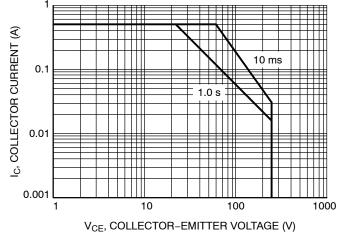


Figure 4. "ON" Voltages



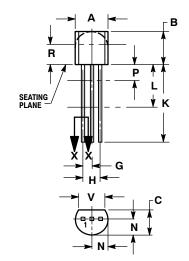


#### PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 029-11 **ISSUE AM** 

STRAIGHT LEAD

**BULK PACK** 



Α

R

Τ SEATING Ρ

B



**SECTION X-X** 

**BENT LEAD** 

TAPE & REEL

AMMO PACK

.1

SECTION X-X

NOTES

DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

- CONTROLLING DIMENSION: INCH. CONTOUR OF PACKAGE BEYOND DIMENSION R 3.
- IS UNCONTROLLED. LEAD DIMENSION IS UNCONTROLLED IN P AND 4 BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
Г	0.250		6.35	
Ν	0.080	0.105	2.04	2.66
Ρ		0.100		2.54
R	0.115		2.93	
V	0.135		3.43	

STYLE 14: PIN 1. EMITTER

2. COLLECTOR BASE 3.

NOTES

2.

- DIMENSIONING AND TOLERANCING PER 1.
- ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.
- 3 CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM. 4

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
Κ	12.70		
N	2.04	2.66	
Ρ	1.50	4.00	
R	2.93		
V	3.43		

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Marginary Marginary   Marginary	Market	Marchine Marchine Image: Control of the sector of the sec	





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